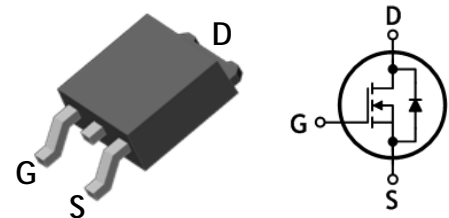


SWITCHING REGULATOR APPLICATION

Features

- High voltage: $BV_{DSS}=600V$ (Min.)
- Low gate charge: $Q_g=12nC$ (Typ.)
- Low drain-source On resistance: $R_{DS(on)}=2.5\Omega$ (Max.)
- RoHS compliant device
- Halogen free package

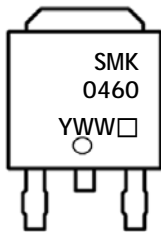


Ordering Information

| Part Number | Marking | Package |
|-------------|---------|---------|
| SMK0460D | SMK0460 | TO-252 |

TO-252

Marking Information



Column 1, 2: Device Code
 Column 3: Production Information
 e.g.) YWW□
 -. YWW: Date Code (year, week)
 -. □: Factory Code ('A': AUK, 'S': SP Semi.)

Absolute maximum ratings ($T_c=25^\circ C$ unless otherwise noted)

| Characteristic | Symbol | Rating | Unit | |
|--|-----------|-------------------|------------|---|
| Drain-source voltage | V_{DSS} | 600 | V | |
| Gate-source voltage | V_{GSS} | ± 30 | V | |
| Drain current (DC) * | I_D | $T_c=25^\circ C$ | 4 | A |
| | | $T_c=100^\circ C$ | 2.53 | A |
| Drain current (Pulsed) * | I_{DM} | 16 | A | |
| Avalanche current ^(Note 2) | I_{AS} | 4 | A | |
| Single pulsed avalanche energy ^(Note 2) | E_{AS} | 225 | mJ | |
| Repetitive avalanche current ^(Note 1) | I_{AR} | 4 | A | |
| Repetitive avalanche energy ^(Note 1) | E_{AR} | 10 | mJ | |
| Power dissipation | P_D | 48 | W | |
| Junction temperature | T_J | 150 | $^\circ C$ | |
| Storage temperature range | T_{stg} | -55~150 | $^\circ C$ | |

* Limited only maximum junction temperature

Thermal Characteristics

| Characteristic | Symbol | Rating | Unit |
|---|---------------|-----------|------|
| Thermal resistance, junction to case | $R_{th(j-c)}$ | Max. 2.6 | °C/W |
| Thermal resistance, junction to ambient | $R_{th(j-a)}$ | Max. 62.5 | |

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---------------------------------------|--------------|--|------|------|-----------|---------------|
| Drain-source breakdown voltage | BV_{DSS} | $I_D=250\mu\text{A}, V_{GS}=0$ | 600 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=250\mu\text{A}, V_{DS}=V_{GS}$ | 2.0 | - | 4.0 | V |
| Drain-source cut-off current | I_{DSS} | $V_{DS}=600\text{V}, V_{GS}=0\text{V}$ | - | - | 1 | μA |
| Gate leakage current | I_{GSS} | $V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$ | - | - | ± 100 | nA |
| Drain-source on-resistance | $R_{DS(ON)}$ | $V_{GS}=10\text{V}, I_D=2\text{A}$ | - | 2.1 | 2.5 | Ω |
| Internal gate resistance | R_G | $f=1\text{MHz}, V_{DS}=0\text{V}$ | - | 1.25 | 6.25 | Ω |
| Forward transfer conductance (Note 3) | g_{fs} | $V_{DS}=10\text{V}, I_D=2\text{A}$ | - | 4.0 | - | S |
| Input capacitance | C_{iss} | $V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$ | - | 670 | 848 | pF |
| Output capacitance | C_{oss} | | - | 57 | 71 | |
| Reverse transfer capacitance | C_{rss} | | - | 9.8 | 12.2 | |
| Turn-on delay time (Note 3,4) | $t_{d(on)}$ | $V_{DD}=300\text{V}, I_D=4\text{A}, R_G=25\Omega$ | 12 | 25 | 38 | ns |
| Rise time (Note 3,4) | t_r | | 14 | 28 | 42 | |
| Turn-off delay time (Note 3,4) | $t_{d(off)}$ | | 55 | 110 | 165 | |
| Fall time (Note 3,4) | t_f | | 18 | 36 | 54 | |
| Total gate charge (Note 3,4) | Q_g | $V_{DS}=480\text{V}, V_{GS}=10\text{V}, I_D=4\text{A}$ | - | 12 | 15 | nC |
| Gate-source charge (Note 3,4) | Q_{gs} | | - | 4 | - | |
| Gate-drain charge (Note 3,4) | Q_{gd} | | - | 3 | - | |

Source-Drain Diode Ratings and Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|------------------------------------|----------|---|------|------|------|---------------|
| Source current (DC) | I_S | Integral reverse diode in the MOSFET | - | - | 4 | A |
| Source current (Pulsed) | I_{SM} | | - | - | 16 | A |
| Forward voltage | V_{SD} | $V_{GS}=0\text{V}, I_S=4\text{A}$ | - | - | 1.4 | V |
| Reverse recovery time (Note 3,4) | t_{rr} | $I_S=4\text{A}, V_{GS}=0\text{V}, di_S/dt=-100\text{A}/\mu\text{s}$ | - | 300 | - | ns |
| Reverse recovery charge (Note 3,4) | Q_{rr} | | - | 2.2 | - | μC |

Note:

1. Repeated rating: Pulse width limited by safe operating area
2. $L=25.9\text{mH}, I_{AS}=4\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
3. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature typical characteristics

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

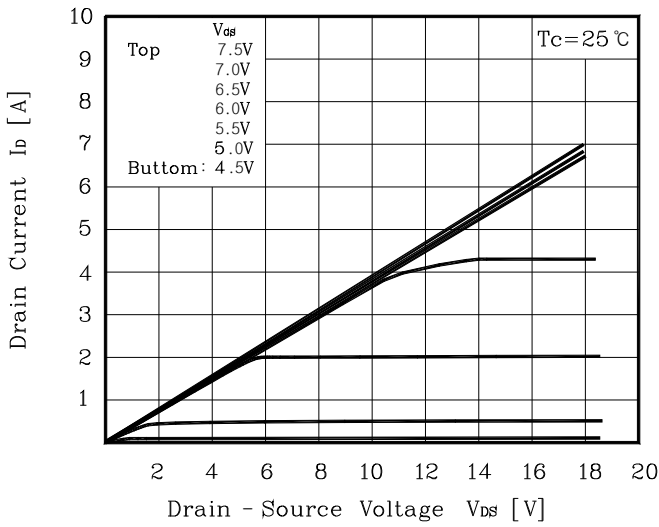


Fig. 2 $I_D - V_{GS}$

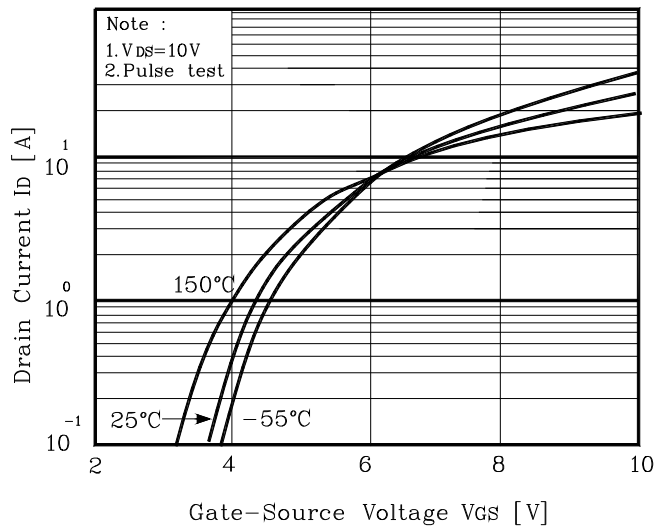


Fig. 3 $R_{DS(ON)} - I_D$

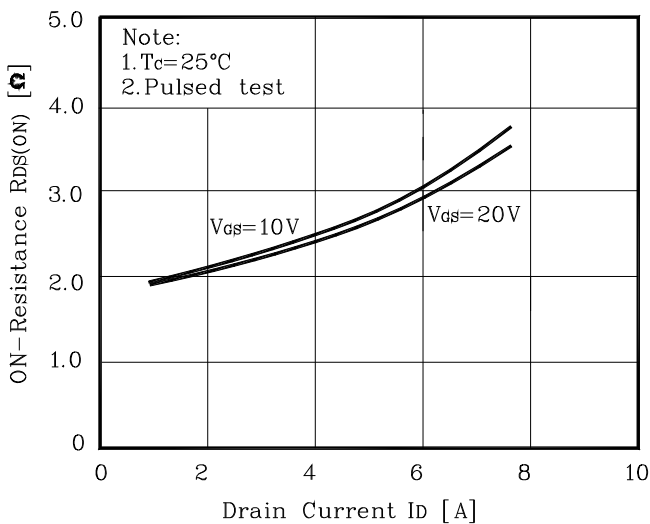


Fig. 4 $I_S - V_{SD}$

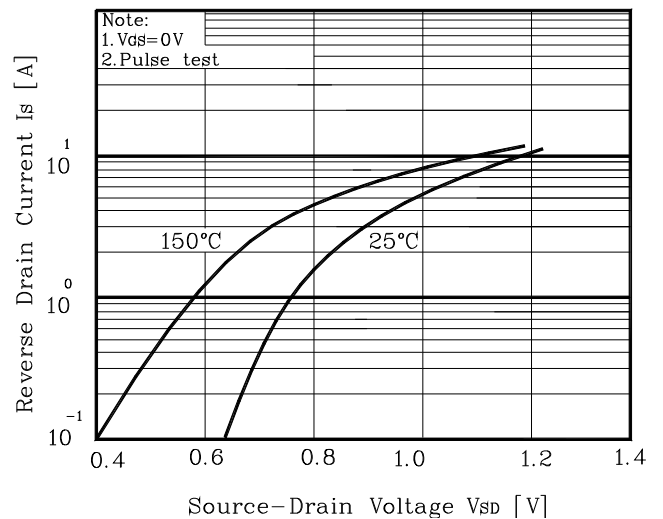


Fig. 5 Capacitance - V_{DS}

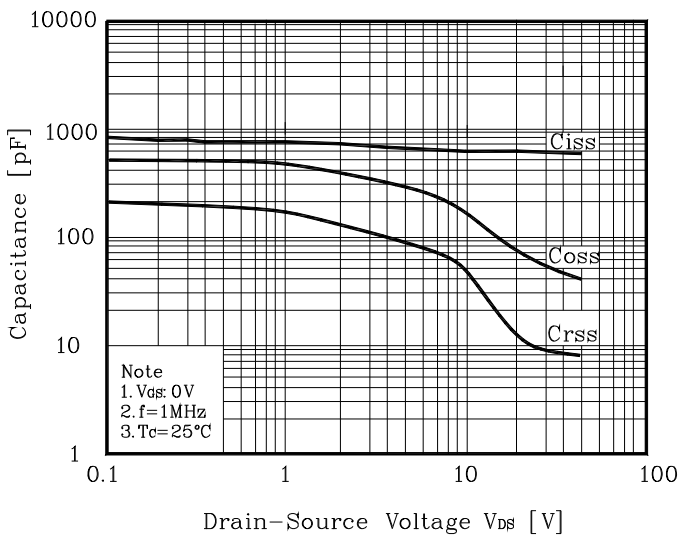
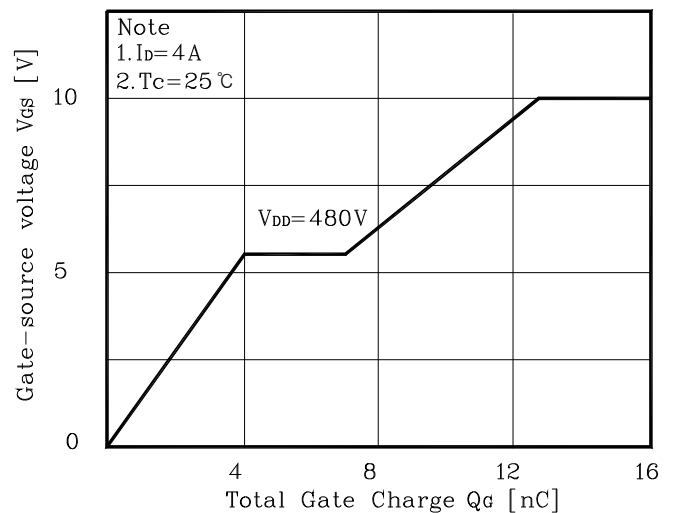


Fig. 6 $V_{GS} - Q_G$



Electrical Characteristic Curves (Continue)

Fig. 7 $BV_{DSS} - T_J$

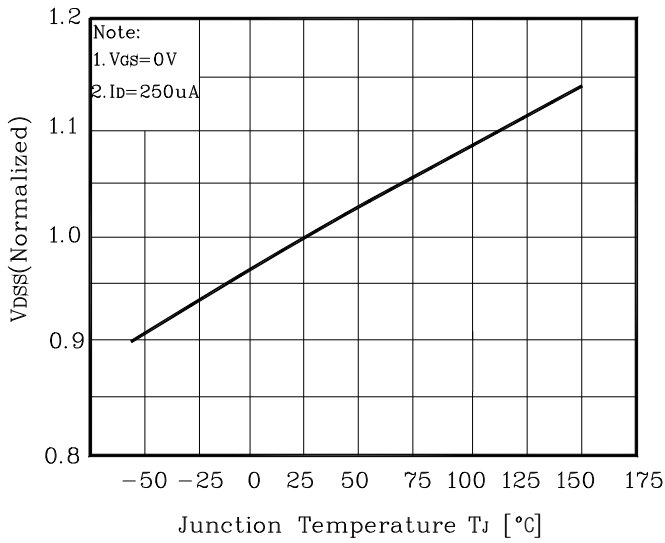


Fig. 8 $R_{DS(ON)} - T_J$

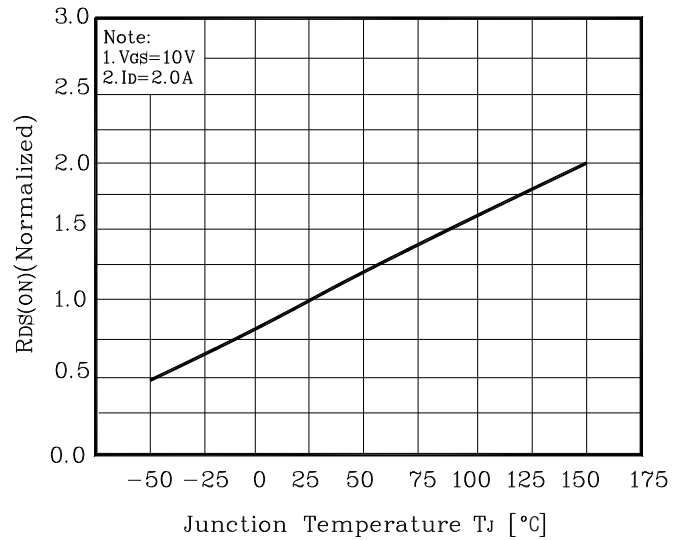


Fig. 9 $I_D - T_C$

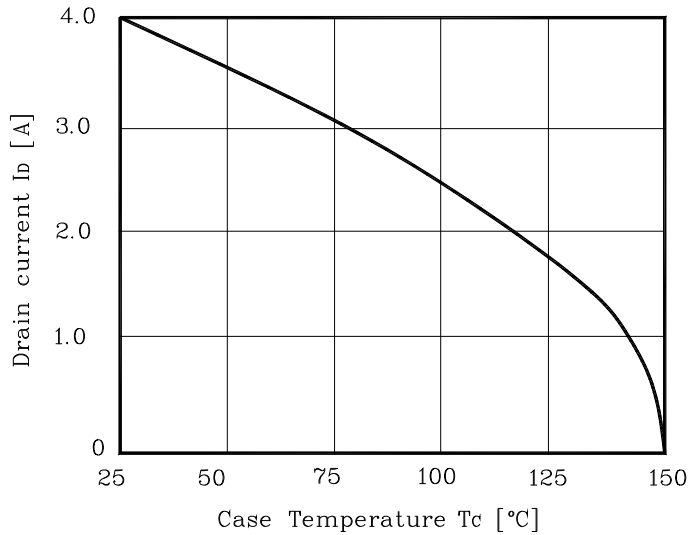


Fig. 10 Safe Operating Area

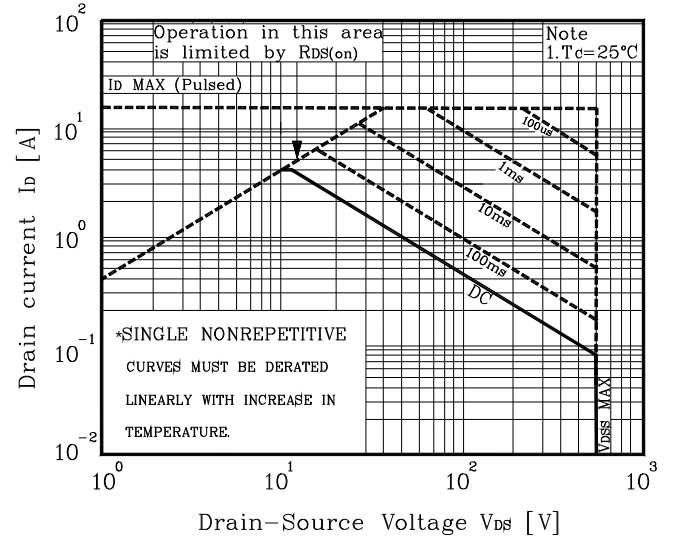


Fig. 11 Gate Charge Test Circuit & Waveform

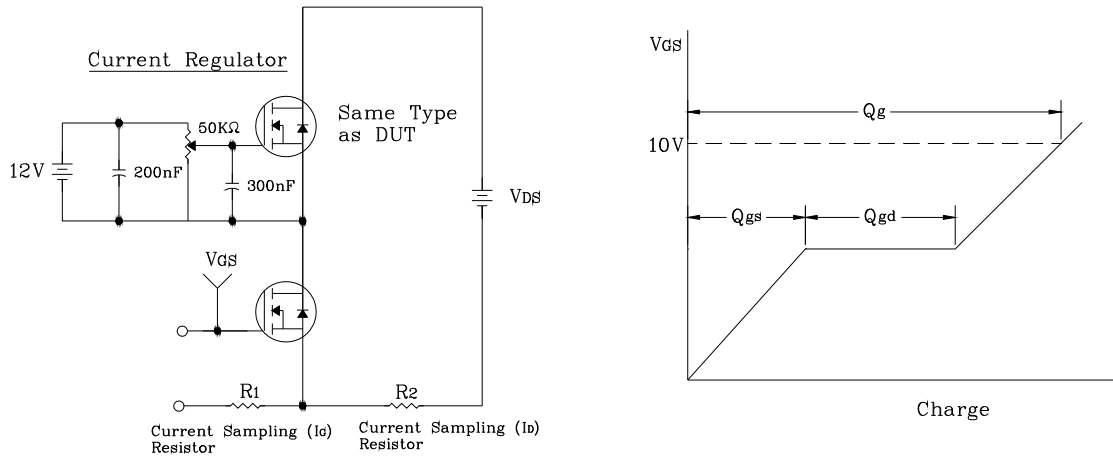


Fig. 12 Resistive Switching Test Circuit & Waveform

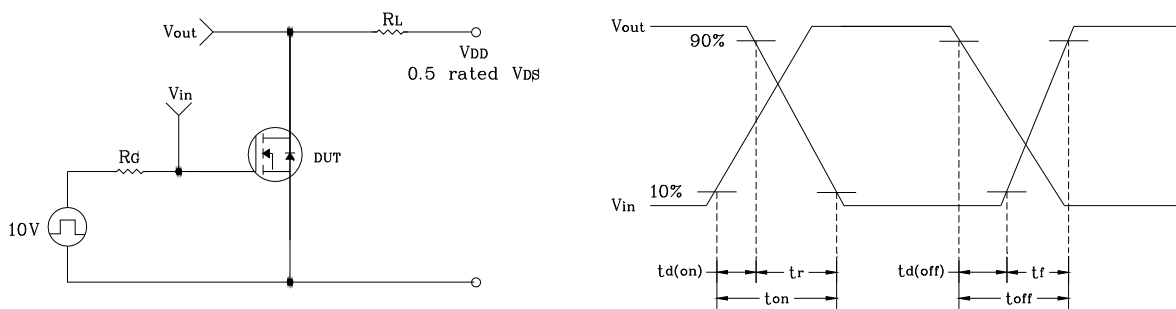


Fig. 13 E_{AS} Test Circuit & Waveform

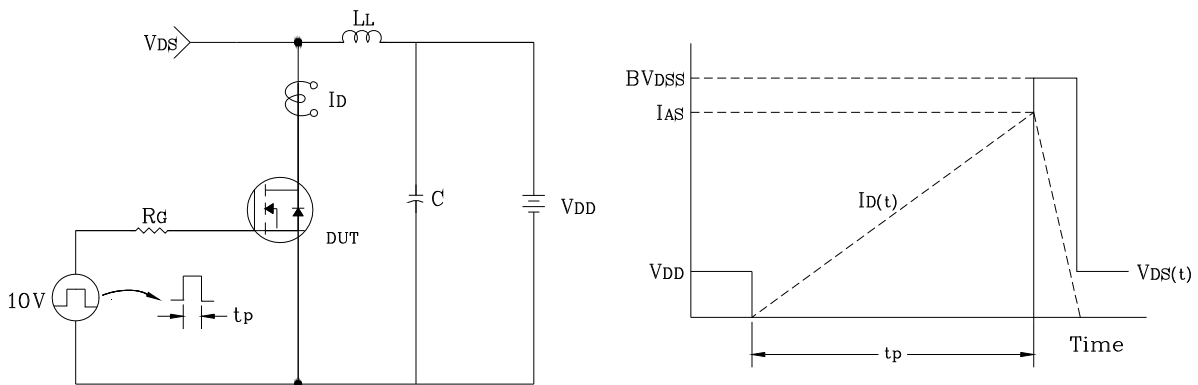
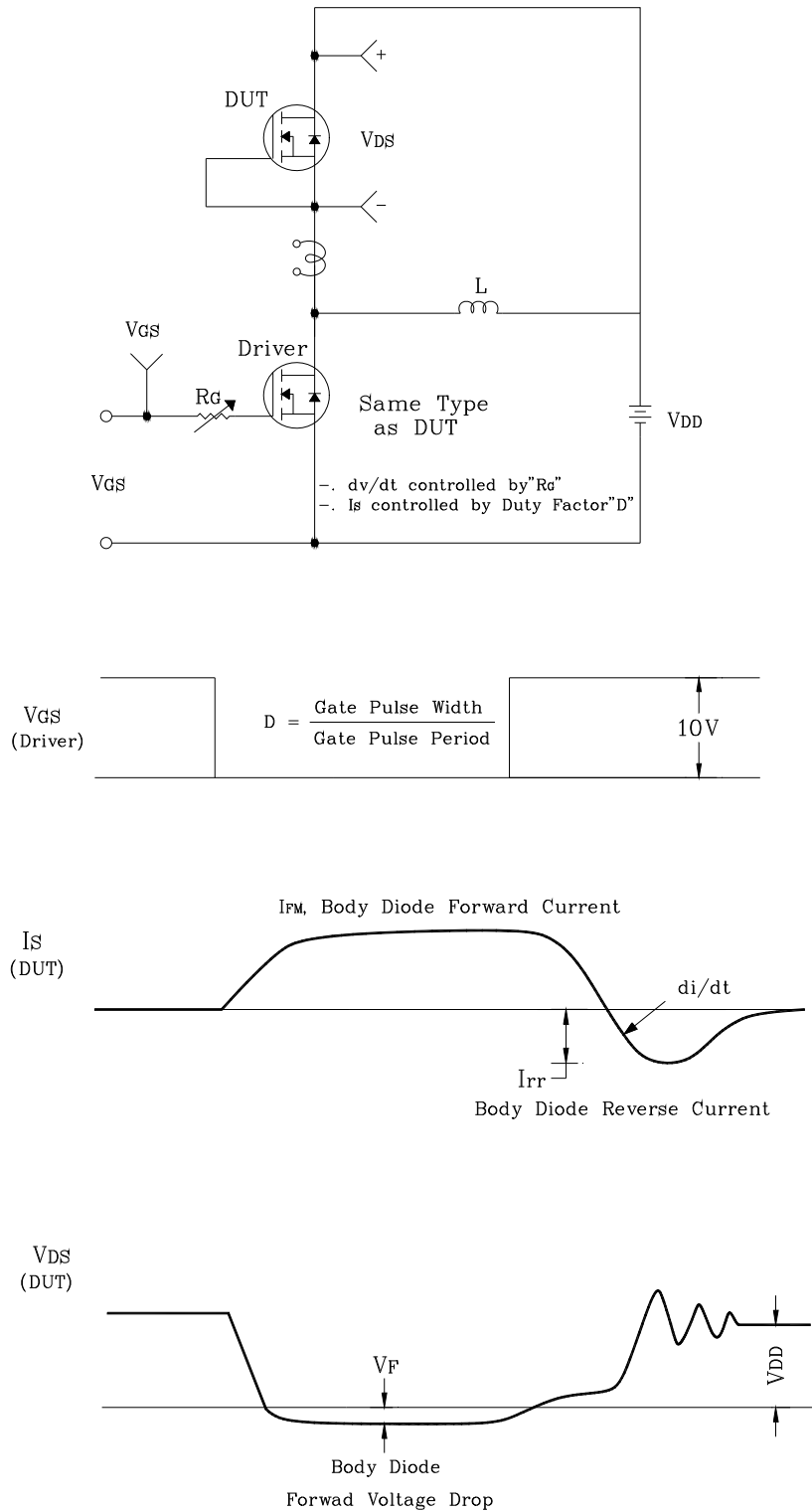


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



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